



Serial EEPROM Series Automotive EEPROM 105°C Operation Microwire BUS EEPROM (3-Wire)

BR93Axx-WM (1K 2K 4K 8K 16K)

General Description

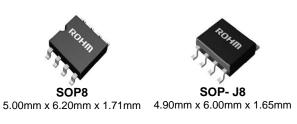
BR93Axx-WM is serial EEPROM of serial 3-line interface method.

Features

- 3-line communications of chip select, serial clock, serial data input / output (the case where input and output are shared)
- Wide temperature range -40°C to +105°C
- Operations available at high speed 2MHz clock(2.5V to 5.5V)
- Speed write available (write time 5ms max.)
- Same package and pin layout from 1Kbit to 16Kbit
- 2.5V to 5.5V single power source operation
- Address auto increment function at read operation
- Write mistake prevention function
 - Write prohibition at power on
 - Write prohibition by command code
 - Write mistake prevention function at low voltage
- Program cycle auto delete and auto end function
- Program condition display by READY / BUSY
- Low current consumption
 - > At write operation (at 5V) : 1.2mA (Typ.)
 - At read operation (at 5V) : 0.3mA (Typ.)
 - At standby condition (at 5V) : 0.1µA (Typ.)(CMOS input)
- TTL compatible (input / output s)
- Data retention for 40 years(Ta≦25°C)
- Endurance up to 1,000,000 times(Ta≦25°C)
- Data at shipment all addresses FFFFh
- AEC-Q100 Qualified

BR93Axx-WM

Packages W(Typ.) x D(Typ.) x H(Max.)







TSSOP-B8

MSOP8 3.00mm x 6.40mm x 1.20mm 2.90mm x 4.00mm x 0.90mm

	Pa	ckage type		SC)P8	SOF	р-18	TSSOP-B8	MSOP8
Capacity	Bit format	Туре	Power source voltage	F	RF	FJ	RFJ	RFVT	RFVM
1Kbit	64×16	BR93A46-WM	2.5V to 5.5V	•	•	•	•	•	•
2Kbit	128×16	BR93A56-WM	2.5V to 5.5V	•	•	•	•	•	•
4Kbit	256×16	BR93A66-WM	2.5V to 5.5V	•	•	•	•	•	•
8Kbit	512×16	BR93A76-WM	2.5V to 5.5V	•	•	•	•	•	•
16Kbit	1K×16	BR93A86-WM	2.5V to 5.5V	۲		•		•	•

OProduct structure : Silicon monolithic integrated circuit OThis product is not designed protection against radioactive rays

● Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	Remarks
Supply voltage	Vcc	-0.3 to +6.5	V	
		0.45 (SOP8)		When using at Ta=25°C or higher, 4.5mW to be reduced per 1°C.
Permissible	Dd	0.45 (SOP-J8)	w	When using at Ta=25°C or higher, 4.5mW to be reduced per 1°C.
dissipation	Pd	0.33 (TSSOP-B8)	vv	When using at Ta=25°C or higher, 3.3mW to be reduced per 1°C.
		0.31 (MSOP8)		When using at Ta=25°C or higher, 3.1mW to be reduced per 1°C.
Storage temperature range	Tstg	-65 to +125	°C	
Operating temperature range	Topr	-40 to +105	°C	
Terminal voltage	-	-0.3 to Vcc+0.3	V	

●Memory Cell Characteristics (Vcc=2.5V to 5.5V)

Parameter		Limit		Unit	Condition	
Falameter	Min.	Тур.	Max.	Unit	Condition	
	1,000,000	-	-		Ta≦25°C	
Endurance ^{*1}	550,000			Times	Ta≦60°C	
Endurance	200,000			Times	Ta≦85°C	
	100,000	-	-		Ta≦105°C	
Data retention ^{*1}	40	-	-	Years	Ta≦25°C	
	10	-	-	reals	Ta≦105°C	

OShipment data all address FFFFh

*1 : Not 100% TESTED

Recommended Operating Ratings

Parameter	Symbol	Limits	Unit
Power source voltage	Vcc	2.5 to 5.5	N/
Input voltage	Vin	0 to Vcc	V

• Electrical Characteristics

(Unless otherwise specified, Vcc=2.5V to 5.5V, Ta=-40°Cto +105°C)

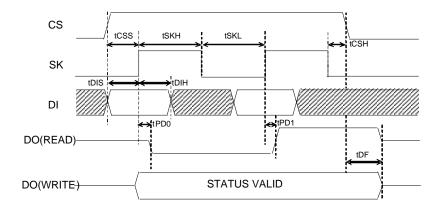
Doromotor	Sumbol		Limits		Linit	Condition
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
"L" input voltage 1	VIL1	-0.3	-	0.8	V	4.0V≦Vcc≦5.5V
"L" input voltage 2	VIL2	-0.3	-	0.2 x Vcc	V	Vcc≦4.0V
"H" input voltage 1	VIH1	2.0	-	Vcc+0.3	V	4.0V≦Vcc≦5.5V
"H" input voltage 2	VIH2	0.7 x Vcc	-	Vcc+0.3	V	Vcc≦4.0V
"L" output voltage 1	VOL1	0	-	0.4	V	IoL=2.1mA, 4.0V≦Vcc≦5.5V
"L" output voltage 2	Vol2	0	-	0.2	V	ΙοL=100μΑ
"H" output voltage 1	VOH1	2.4	-	Vcc	V	IOH=-0.4mA, 4.0V≦Vcc≦5.5V
"H" output voltage 2	Voh2	Vcc-0.2	-	Vcc	V	Іон=-100μА
Input leak current	ILI	-1	-	1	μA	VIN=0V to Vcc
Output leak current	Ilo	-1	-	1	μA	VOUT=0V to Vcc, CS=0V
	ICC1	-	-	3.0	mA	fsk=2MHz, tE/W=5ms (WRITE)
Current consumption	ICC2	-	-	1.5	mA	fsk=2MHz (READ)
	Іссз	-	-	4.5	mA	fsk=2MHz, tE/W=5ms (WRAL, ERAL)
Standby current	lsв	-	-	2	μA	CS=0V, DO=OPEN

•Operating Timing Characteristics

(Ta=-40°C to +105°C, Vcc=2.5V to 5.5V)

Parameter	Symbol	2.5	5V≦Vcc≦5	.5V	Unit
Farameter	Symbol	Min.	Тур.	Max.	Unit
SK frequency	fsк	-	-	2	MHz
SK "H" time	t _{sкн}	230	-	-	ns
SK "L" time	t _{SKL}	230	-	-	ns
CS "L" time	t _{cs}	200	-	-	ns
CS setup time	t _{CSS}	50	-	-	ns
DI setup time	t _{DIS}	100	-	-	ns
CS hold time	t _{CSH}	0	-	-	ns
DI hold time	t _{DIH}	100	-	-	ns
Data "1" output delay time	t _{PD1}	-	-	200	ns
Data "0" output delay time	t _{PD0}	-	-	200	ns
Time from CS to output establishment	t _{SV}	-	-	150	ns
Time from CS to High-Z	t _{DF}	-	-	150	ns
Write cycle time	t _{E/W}	-	-	5	ms

•Sync Data Input / Output Timing

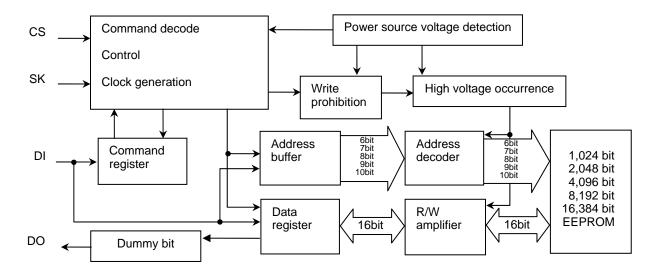


OData is taken by DI sync with the rise of SK.

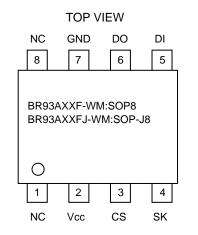
OAt read operation, data is output from DO in sync with the rise of SK.

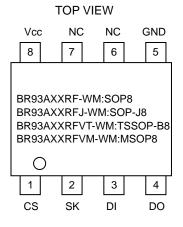
OThe status signal at write (READY / BUSY) is output after tCS from the fall of CS after write command input, at the area DO where CS is "H", and valid until the next command start bit is input. And, while CS is "L", DO becomes High-Z. OAfter completion of each mode execution, set CS "L" once for internal circuit reset, and execute the following operation mode.

Block Diagram



Pin Configurations





Pin Descriptions

Pin name	I/O	Function
Vcc	-	Power source
GND	-	All input / output reference voltage, 0V
CS	Input	Chip select input
SK	Input	Serial clock input
DI	Input	Start bit, ope code, address, and serial data input
DO	Output	Serial data output, READY / BUSY internal condition display output
NC	-	Non connected terminal, Vcc, GND or OPEN

•Typical Performance Curves

(The following characteristic data are typ. values.)

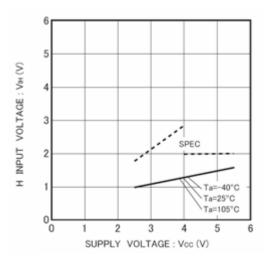


Figure 1. H input voltage VIH (CS, SK, DI)

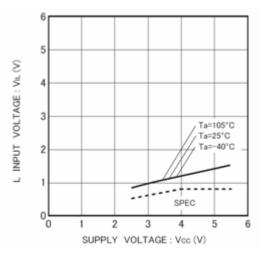


Figure 2. L input voltage VIL (CS,SK,DI)

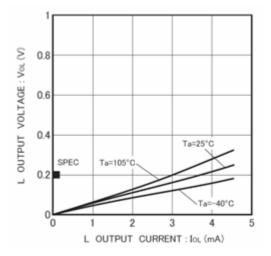


Figure 3. L output voltage VOL-IOL (Vcc=2.5V)

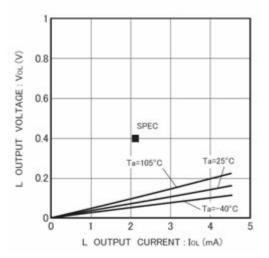


Figure 4. L output voltage VOL-IOL (Vcc=4.0V)

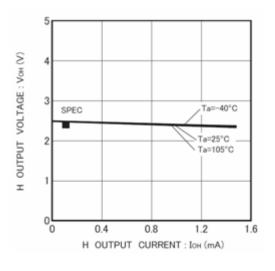


Figure 5. H output voltage VOH-IOH

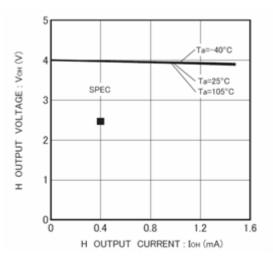


Figure 6. H output voltage VOH-IOH (Vcc=4.0V)

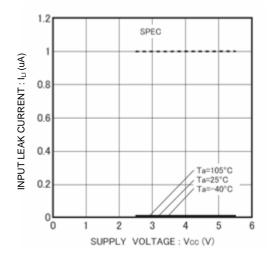


Figure 7. Input leak current ILI (CS, SK, DI)

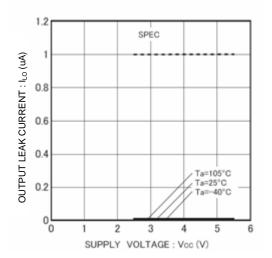


Figure 8. Output leak current ILO (DO)

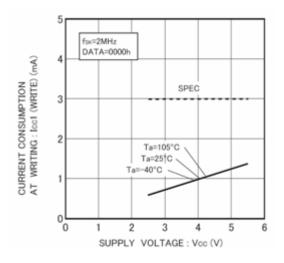


Figure 9. Current consumption at WRITE operation Icc1 (WRITE, fSK=2MHz)

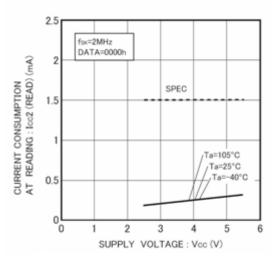


Figure 10. Consumption current at READ operation Icc2 (READ, fSK=2MHz)

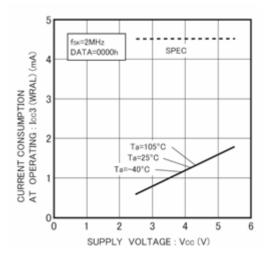


Figure 11. Consumption current at WRAL operation Icc3 (WRAL, fSK=2MHz)

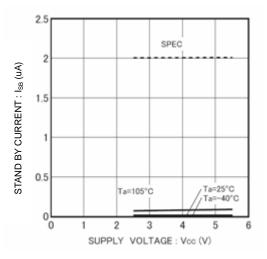


Figure 12. Consumption current at standby ISB

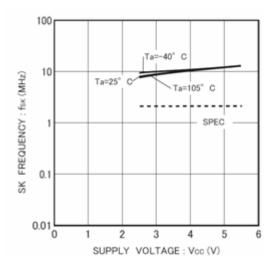


Figure 13. SK frequency fSK

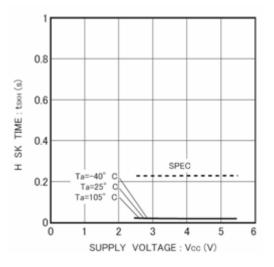
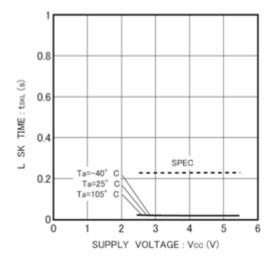
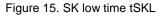


Figure 14. SK high time tSKH





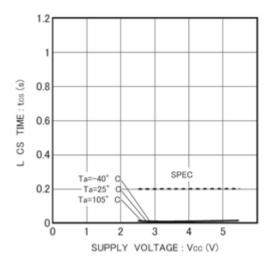


Figure 16. CS low time tCS

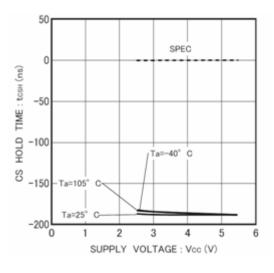


Figure 17. CS hold time tCSH

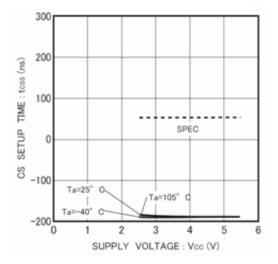


Figure 18. CS setup time tCSS

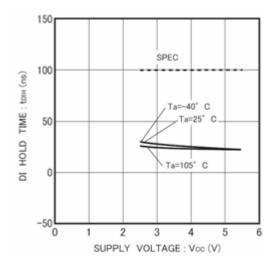


Figure 19. DI hold time tDIH

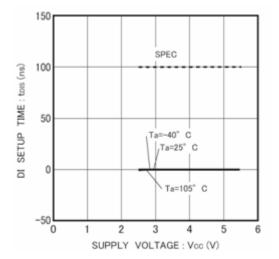


Figure 20. DI setup time tDIS

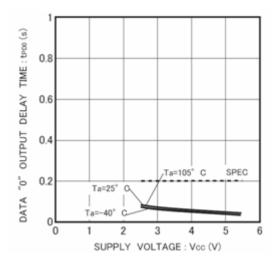


Figure 21. Data "0" output delay time tPD0

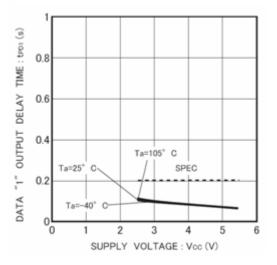


Figure 22. Output data "1" delay time tPD1

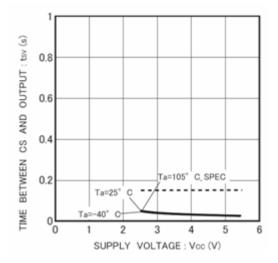


Figure 23. Time from CS to output establishment tSV

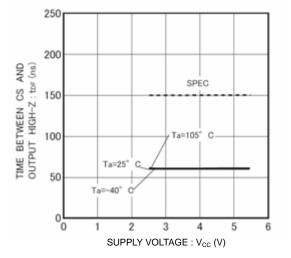


Figure 24. Time from CS to High-Z tDF

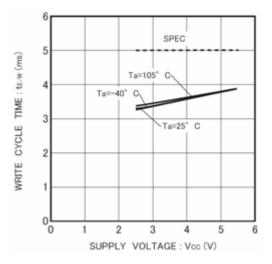


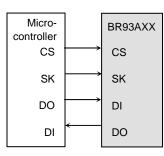
Figure 25. Write cycle time tE/W

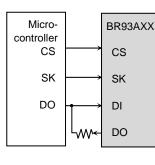
Description of Operations

Communications of the Microwire Bus are carried out by SK (serial clock), DI (serial data input), DO (serial data output), and CS (chip select) for device selection.

When to connect one EEPROM to a microcontroller, connect it as shown in Figure 26 (a) or Figure 26 (b). When to use the input and output common I/O port of the microcontroller, connect DI and DO via a resistor as shown in Figure 26 (b) (Refer to page18.), and connection by 3 lines is available.

In the case of plural connections, refer to Figure 26 (c).





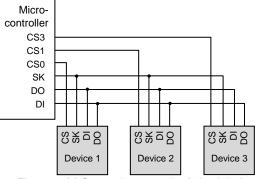
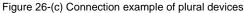


Figure 26-(a) Connection by 4 lines

Figure 26-(b) Connection by 3 lines



A7 of BR93A56-WM becomes Don't Care.

A9 of BR93A76-WM becomes Don't Care.

Figure 26. Connection method with microcontroller

Communications of the Microwire Bus are started by the first "1" input after the rise of CS. This input is called a start bit. After input of the start bit, input ope code, address and data. Address and data are input all in MSB first manners. "0" input after the rise of CS to the start bit input is all ignored. Therefore, when there is limitation in the bit width of PIO of the microcontroller, input "0" before the start bit input, to control the bit width.

Command Mode

		Start	Ope		Address						
Command		bit	code	BR93A46-WM	BR93A56/66-WM	BR93A76/86-WM	Data				
Read (READ)	*1	1	10	A5,A4,A3,A2,A1,A0	A7,A6,A5,A4,A3,A2,A1,A0	A9,A8,A7,A6,A5,A4,A3,A2,A1,A0	D15 to D0(READ DATA)				
Write enable (WEN)		1	00	1 1 * * * *	1 1 * * * * * *	1 1 * * * * * * * *					
Write (WRITE)	*2	1	01	A5,A4,A3,A2,A1,A0	A7,A6,A5,A4,A3,A2,A1,A0	A9,A8,A7,A6,A5,A4,A3,A2,A1,A0	D15 to D0(WRITE DATA)				
Write all (WRAL)	*2	1	00	0 1 * * * *	0 1 * * * * * *	0 1 * * * * * * * *	D15 to D0(WRITE DATA)				
Write disable (WDS)		1	00	0 0 * * * *	0 0 * * * * * *	0 0 * * * * * * * *					
Erase (ERASE)		1	11	A5,A4,A3,A2,A1,A0	A7,A6,A5,A4,A3,A2,A1,A0	A9,A8,A7,A6,A5,A4,A3,A2,A1,A0					
Chip erase (ERAL)		1	00	1 0 * * * *	1 0 * * * * * *	1 0 * * * * * * * *					

· Input the address and the data in MSB first manners.

As for *, input either VIH or VIL.

*Start bit

Acceptance of all the commands of this IC starts at recognition of the start bit.

The start bit means the first "1" input after the rise of CS.

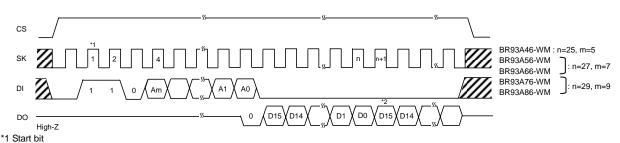
*1 As for read, by continuous SK clock input after setting the read command, data output of the set address starts, and

address data in significant order are sequentially output continuously. (Auto increment function)

*2 When the read and the write all commands are executed, data written in the selected memory cell is automatically deleted, and input data is written.

•Timing Chart

1) Read cycle (READ)

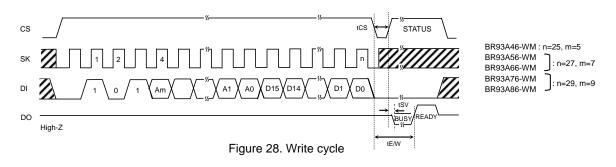


When data "1" is input for the first time after the rise of CS, this is recognized as a start bit. And when "1" is input after plural "0" are input, it is recognized as a start bit, and the following operation is started. This is common to all the commands to described hereafter.

Figure 27. Read cycle

OWhen the read command is recognized, input address data (16bit) is output to serial. And at that moment, at taking A0, in sync with the rise of SK, "0" (dummy bit) is output. And, the following data is output in sync with the rise of SK. This IC has an address auto increment function valid only at read command. This is the function where after the above read execution, by continuously inputting SK clock, the above address data is read sequentially. And, during the auto increment, keep CS at "H".

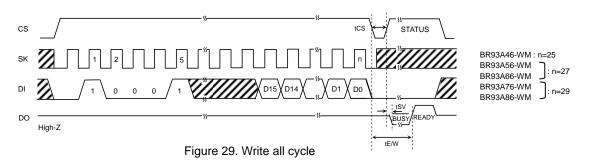
2) Write cycle (WRITE)



OIn this command, input 16bit data (D15 to D0) are written to designated addresses (Am to A0). The actual write starts by the fall of CS of D0 taken SK clock.

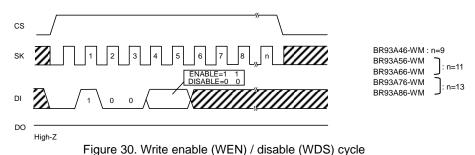
When STATUS is not detected, (CS="L" fixed) Max. 5ms in conformity with tE/W, and when STATUS is detected (CS="H"), all commands are not accepted for areas where "L" (\overline{BUSY}) is output from D0, therefore, do not input any command.

3) Write all cycyle (WRAL)



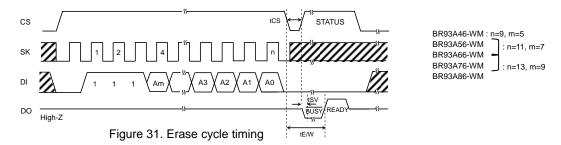
OIn this command, input 16bit data is written simultaneously to all adresses. Data is not written continuously per one word but is written in bulk, the write time is only Max. 5ms in conformity with tE/W.

4) Write enable (WEN) / disable (WDS) cycle



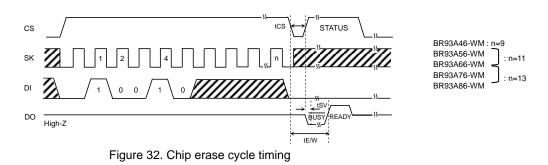
O At power on, this IC is in write disable status by the internal RESET circuit. Before executing the write command, it is necessary to execute the write enable command. And, once this command is executed, it is valid unit the write disable command is executed or the power is turned off. However, the read command is valid irrespective of write enable / diable command. Input to SK after 6 clocks of this command is available by either "H" or "L", but be sure to input it.

- O When the write enable command is executed after power on, write enable status gets in. When the write disable command is executed then, the IC gets in write disable status as same as at power on, and then the write command is canceled thereafter in software manner. However, the read command is executable. In write enable status, even when the write command is input by mistake, write is started. To prevent such a mistake, it is recommended to execute the write disable command after completion of write.
- 5) Erase cycle timing (ERASE)



OIn this command, data of the designated address is made into "1". The data of the designated address becomes "FFFFh". Actual ERASE starts at the fall of CS after the fall of A0 taken SK clock. In ERASE, status can be detected in the same manner as in WRITE command.

6) Chip erase cycle timing (ERAL)



OIn this command, data of all addresses is erased. Data of all addresses becomes "FFFFh". Actual ERASE starts at the fall of CS after the fall of the n-th clock from the start bit input. In ERAL, status can be detected in the same manner as in WRITE command.

Application

1) Method to cancel each command

Start bit				(In the eed	
	Ope code	Address ^{*1}	Data	(in the cas	se of BR93A46-WM)
1bit	2bit	6bit	16bit		
		all areas in read mod	le. \longrightarrow		8 bits in BR93A56-WM, BR93A66-WM I0 bits in BR93A76-WM, BR93A86-WM
 Method to car 	ncel : cancel by CS	="L"			
Figure 33	3. READ cance	I available timing	g		
		(• 25 Rise of clock	*2	
VRITE, WRAI	L				
			SK24[25[_		
		Ć	Enlarged fi	igure	
		*1	_		
Start bit	Ope code	Address	Data	tE/W	(In the case of BR93A46-WM)
1bit	2bit	6bit - a ———	16bit	← b —	
25 CIOCK FISE ANC	d after** ot available by any	moons If Vcc is moo	to OFF in this groa	29 clo	cks in BR93A56-WM, BR93A66-WM cks in BR93A76-WM BR93A86-WM
designated addre	ot available by any ess data is not guar	means. If Vcc is mad anteed, therefore wri busly, cancellation is	ite once again.	29 clo	
Cancellation is no designated addre	ot available by any ess data is not guar	anteed, therefore wri	ite once again.	, 29 clo	
Cancellation is no designated addre	ot available by any ess data is not guar	anteed, therefore wri	ite once again. not available. 29 Rise of clock	, 29 clo	
Cancellation is no designated addre	ot available by any ess data is not guar	anteed, therefore wri	ite once again. not available.	, 29 clo	
Cancellation is no designated addre	ot available by any ess data is not guar	anteed, therefore wri	ite once again. not available. 29 Rise of clock SK2829	, *2 [30]31	
Cancellation is no designated addre	ot available by any ess data is not guar	anteed, therefore wri	ite once again. not available. 29 Rise of clock SK2829 DI D1	29 clor	
Cancellation is n designated addre And when SK clc	ot available by any ess data is not guar ock is input continuc	anteed, therefore wri busly, cancellation is	ite once again. not available. 29 Rise of clock SK2829 DI1 aCb = Enlarged f	29 clos	cks in BR93A76-WM BR93A86-WM
Cancellation is n designated addre And when SK clc Start bit	ot available by any ess data is not guar ock is input continuc	anteed, therefore wri busly, cancellation is	ite once again. not available. 29 Rise of clock SK2829 DI1 Enlarged f Data	29 clor	
Cancellation is n designated addre And when SK clc	ot available by any ess data is not guar ock is input continuc	anteed, therefore wri busly, cancellation is	ite once again. not available. 29 Rise of clock SK2829 DI1 aCb = Enlarged f	29 clos	cks in BR93A76-WM BR93A86-WM
Cancellation is n designated addre And when SK clo Start bit 1bit	ot available by any ess data is not guar ock is input continue Ope code 2bit	anteed, therefore wri busly, cancellation is	ite once again. not available. 29 Rise of clock SK2829 DI1 Enlarged f Data	29 clos	cks in BR93A76-WM BR93A86-WM
Cancellation is n designated addre And when SK clc Start bit	ot available by any ess data is not guar ock is input continue Ope code 2bit 29 clock rise	anteed, therefore wri busly, cancellation is	ite once again. not available. 29 Rise of clock SK2829 DI1 Enlarged f Data	29 clos	cks in BR93A76-WM BR93A86-WM
Cancellation is n designated addre And when SK clc Start bit 1bit From start bit to Cancel by CS=" 29 clock rise an	ot available by any ess data is not guar pock is input continue Ope code 2bit 29 clock rise L" d after	anteed, therefore wri busly, cancellation is	ite once again. not available. 29 Rise of clock SK2829 DI1 00 Enlarged f Data 16bit	29 clor *2 30_31_ igure tE/W c	cks in BR93A76-WM BR93A86-WM

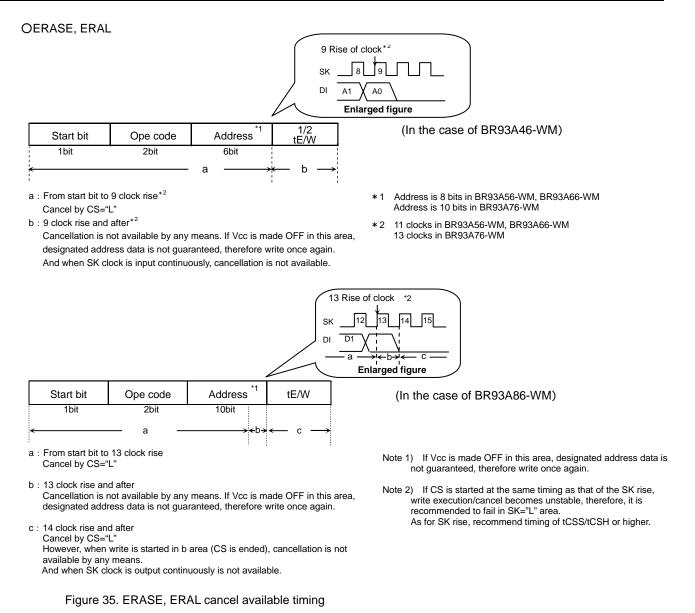
c: 30 clock rise and after

Cancel by CS="L" However, when write is started in b area (CS is ended), cancellation is not available by any means. And when SK clock is output continuously is not available.

Figure 34. WRITE, WRAL cancel available timing

Note 2) If CS is started at the same timing as that of the SK rise, write execution/cancel becomes unstable, therefore, it is recommended to fail in SK="L" area.

As for SK rise, recommend timing of tCSS/tCSH or higher.



2) At standby

OStandby current

When CS is "L", SK input is "L", DI input is "H", and even with middle electric potential, current does not increase.

OTiming

As shown in Figure 36, when SK at standby is "H", if CS is started, DI status may be read at the rise edge. At standby and at power ON/OFF, when to start CS, set SK input or DI input to "L" status. (Refer to Figure 37)

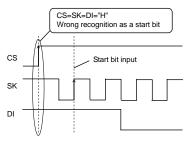


Figure 36. Wrong operating timing

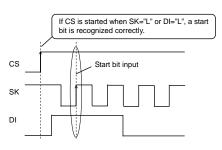


Figure 37. Normal operating timing

3) Equivalent circuit

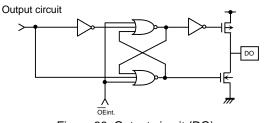


Figure 38. Output circuit (DO)

Input circuit

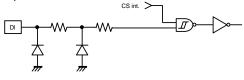
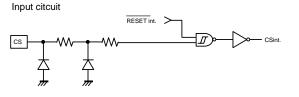


Figure 40. Input circuit (DI)





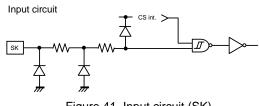


Figure 41. Input circuit (SK)

4) I/O peripheral circuit 4-1) Pull down CS.

By making CS="L" at power ON/OFF, mistake in operation and mistake write are prevented. OPull down resistance Rpd of CS pin

To prevent mistake in operation and mistake write at power ON/OFF, CS pull down resistance is necessary. Select an appropriate value to this resistance value from microcontroller VOH, IOH, and VIL characteristics of this IC.

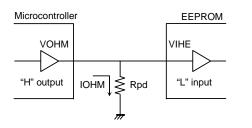


Figure 42. CS pull down resistance

$$\begin{array}{rcl} \mathsf{Rpd} & \geqq & \underbrace{\mathsf{VOHM}}_{\mathsf{IOHM}} & & \ddots & \ddots \\ \mathsf{VOHM} & \geqq & \mathsf{VIHE} & & \ddots & \ddots \\ \end{array}$$

Example) When V_{CC} =5V, VIHE=2V, VOHM=2.4V, IOHM=2mA, from the equation ①,

$$\mathsf{Rpd} \geq \frac{2.4}{2 \times 10^{-3}}$$

 \therefore Rpd \geq 1.2 [k Ω]

With the value of Rpd to satisfy the above equation, VOHM becomes 2.4V or higher, and VIHE (=2.0V), the equation 2 is also satisfied.

- VIHE : EEPROM VIH specifications
- VOHM: Microcontroller VOH specifications
- · IOHM : Microcontroller IOH specifications
- 4-2) DO is available in both pull up and pull down.

Do output become "High-Z" in other READY / BUSY output timing than after data output at read command and write command. When malfunction occurs at "High-Z" input of the microcontroller port connected to DO, it is necessary to pull down and pull up DO. When there is no influence upon the microcontroller operations, DO may be OPEN. If DO is OPEN, and at timing to output status READY, at timing of CS="H", SK="H", DI="H", EEPROM recognizes this as a start bit, resets READY output, and DO="High-Z", therefore, READY signal cannot be detected. To avoid such output, pull up DO pin for improvement.

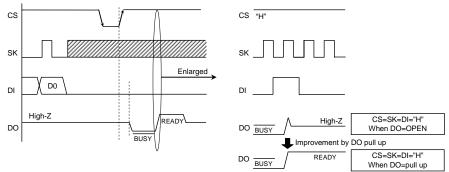


Figure 43. READY output timing at DO=OPEN

OPull up resistance Rpu and pull down resistance Rpd of DO pin

As for pull up and pull down resistance value, select an appropriate value to this resistance value from microcontroller VIH, VIL, and VOH, IOH, VOL, IOL characteristics of this IC.

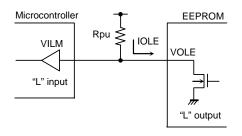


Figure 44. DO pull up resistance

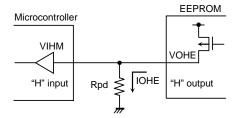
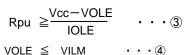


Figure 45. DO pull down resistance



Example) When V_{CC} =5V, VOLE=0.4V, IOLE=2.1mA, VILM=0.8V,

from the equation
$$(3)$$
,
Rpu $\geq \frac{5-0.4}{2.1 \times 10^{-3}}$

 $\therefore \qquad \mathsf{Rpu} \geq 2.2 \, [\mathsf{k}\,\Omega\,]$

With the value of Rpu to satisfy the above equation, VOLE becomes 0.4V or below, and with VILM(=0.8V), the equation 4 is also satisfied.

- VOLE : EEPROM VOL specifications
- · IOLE : EEPROM IOL specifications
- · VILM : Microcontroller VIL specifications

$$\mathsf{Rpd} \geq \frac{\mathsf{VOHE}}{\mathsf{IOHE}} \qquad \cdots 5$$

$$VOHE \ge VIHM \cdots 6$$

Example) When $V_{CC} = 5V$, VOHE=Vcc-0.2V, IOHE=0.1mA, VIHM=Vcc $\times 0.7V$ from the equation (5),

Rpd
$$\geq \frac{5-0.2}{0.1 \times 10^{-3}}$$

Rpd
$$\geq$$
 48 [k Ω]

With the value of Rpd to satisfy the above equation, VOHE becomes 2.4V or below, and with VIHM (=3.5V), the equation 6 is also satisfied.

- VOHE : EEPROM VOH specifications
- IOHE : EEPROM IOH specifications
- · VIHM : Microcontroller VIH specifications
- 5) READY / BUSY status display (DO terminal)

(common to BR93A46-WM, BR93A56-WM, BR93A66-WM, BR93A76-WM, BR93A86-WM) This display outputs the internal status signal. When CS is started after tCS (Min.200ns) from CS fall after write command input, "H" or "L" is output.

 R/\overline{B} display="L" (\overline{BUSY}) = write under execution

(DO status) After the timer circuit in the IC works and creates the period of tE/W, this time circuit completes automatically. And write to the memory cell is made in the period of tE/W, and during this period, other command is not accepted.

 R/\overline{B} display = "H" (READY) = command wait status

(DO status) Even after tE/W (max.5ms) from write of the memory cell, the following command is accepted.

Therefore, CS="H" in the period of tE/W, and when input is in SK, DI, malfunction may occur, therefore, DI="L" in the area CS="H". (Especially, in the case of shared input port, attention is required.)

*Do not input any command while status signal is output. Command input in BUSY area is cancelled, but command input in READY area is accepted. Therefore, status READY output is cancelled, and malfunction and mistake write may be made.

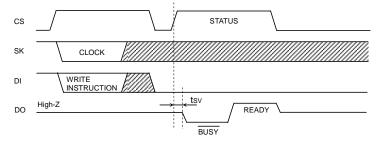


Figure 46. R/B status output timing chart

6) When to directly connect DI and DO

This IC has independent input terminal DI and output terminal DO, and separate signals are handled on timing chart, meanwhile, by inserting a resistance R between these DI and DO terminals, it is possible to carry out control by 1 control line.

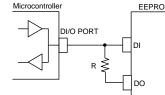


Figure 47. DI, DO control line common connection

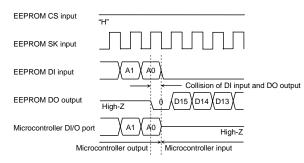
OData collision of microcontroller DI/O output and DO output and feedback of DO output to DI input.

Drive from the microcontroller DI/O output to DI input on I/O timing, and signal output from DO output occur at the same time in the following points.

(1) 1 clock cycle to take in A0 address data at read command

Dummy bit "0" is output to DO terminal.

 \rightarrow When address data A0 = "1" input, through current route occurs.





(2) Timing of CS = "H" after write command. DO terminal in READY / \overline{BUSY} function output.

When the next start bit input is recognized, "HIGH-Z" gets in. →Especially, at command input after write, when CS input is started with microcontroller DI/O output "L",

READY output "H" is output from DO terminal, and through current route occurs.

Feedback input at timing of these (1) and (2) does not cause disorder in basic operations, if resistance R is inserted.

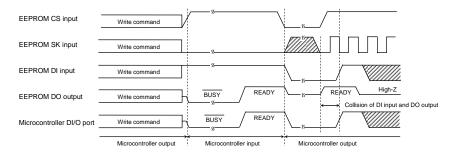
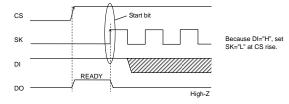
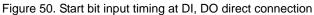


Figure 49. Collision timing at DI, DO direct connection

Note) As for the case (2), attention must be paid to the following. When status READY is output, DO and DI are shared, DI="H" and the microcontroller DI/O="High-Z" or the microcontroller DI/O="H", if SK clock is input, DO output is input to DI and is recognized as a start bit, and malfunction may occur. As a method to avoid malfunction, at status READY output, set SK="L", or start CS within 4 clocks after "H" of READY signal is output.





OSelection of resistance value R

The resistance R becomes through current limit resistance at data collision. When through current flows, noises of power source line and instantaneous stop of power source may occur. When allowable through current is defined as I, the following relation should be satisfied. Determine allowable current amount in consideration of impedance and so forth of power source line in set. And insert resistance R, and set the value R to satisfy EEPROM input level VIH/VIL even under influence of voltage decline owing to leak current and so forth. Insertion of R will not cause any influence upon basic operations.

- (1) Address data A0 = "1" input, dummy bit "0" output timing
 - (When microcontroller DI/O output is "H", EEPROM DO outputs "L", and "H" is input to DI)
 - Make the through current to EEPROM 10mA or below.
 - · See to it that the level VIH of EEPROM should satisfy the following.

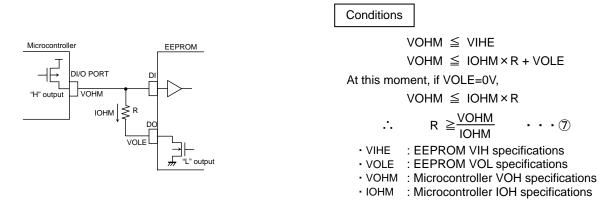
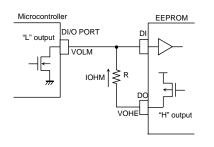


Figure 51. Circuit at DI, DO direct connection (Microcontroller DI/O "H" output, EEPROM "L" output)

(2) DO status READY output timing

(When the microcontroller DI/O is "L", EEPROM DO output "H", and "L" is input to DI)

· Set the EEPROM input level VIL so as to satisfy the following.



Conditions VOLM ≧ VILE VOLM ≧ VOHE – IOLM×R As this moment, VOHE=Vcc VOLM ≧ Vcc – IOLM×R Vcc – VOLM · · · 8 IOLM VILE : EEPROM VIL specifications VOHE : EEPROM VOH specifications : Microcontroller VOL specifications VOLM · IOLM : Microcontroller IOL specifications

Example) When Vcc=5V, VOHM=5V, IOHM=0.4mA, VOLM=5V, IOLM=0.4mA,

From the equation $\overline{\mathcal{O}}$,

From the equation[®],

$R \ge \frac{VOHM}{IOHM}$	$R \geq \frac{Vcc - VOLM}{IOLM}$
$R \ge \frac{5}{0.4 \times 10^{-3}}$	$R \ge \frac{5 - 0.4}{2.1 \times 10^{-3}}$
R ≧ 12.5 [kΩ] ···9	$\therefore \qquad R \geq 2.2 [k \Omega] \qquad \cdots \qquad \textcircled{0}$
	Therefore, from the equations (\mathfrak{Y}) and (\mathfrak{W}) ,
	∴ R ≧ 12.5 [kΩ]

Figure 52. Circuit at DI, DO direct connection (Microcontroller DI/O "L" output, EEPROM "H" output)

.....

7) Notes on power ON/OFF

At power ON/OFF, set CS "L".

When CS is "H", this IC gets in input accept status (active). If power is turned on in this status, noises and the likes may cause malfunction, mistake write or so. To prevent these, at power ON, set CS "L". (When CS is in "L" status, all inputs are cancelled.) And at power decline, owing to power line capacity and so forth, low power status may continue long. At this case too, owing to the same reason, malfunction, mistake write may occur, therefore, at power OFF too, set CS "L".

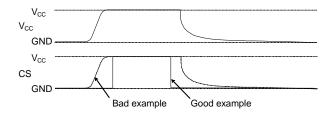


Figure 53. Timing at power ON/OFF

(Bad example) CS pin is pulled up to Vcc.

In this case, CS becomes "H" (active status), and EEPROM may have malfunction, mistake write owing to noise and the likes.

Even when CS input is High-Z, the status becomes like this case, which please note.

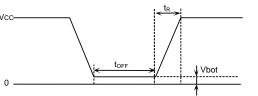
(Good example) It is "L" at power ON/OFF. Set 10ms or higher to recharge at power OFF. When power is turned on without observing this condition, IC internal circuit may not be reset, which please note.

OPOR citcuit

This IC has a POR (Power On Reset) circuit as a mistake write countermeasure. After POR operation, it gets in write disable status. The POR circuit is valid only when power is ON, and does not work when power is OFF. However, if CS is "H" at power ON/OFF, it may become write enable status owing to noises and the likes. For secure operations, observe the following conditions.

1. Set CS="L"

2. Turn on power so as to satisfy the recommended conditions of tR, tOFF, Vbot for POR circuit operation.



Recommended conditions of tR, tOFF, Vbot

t _R	t _{OFF}	Vbot
10ms or below	10ms or higher	0.3V or below
100ms or below	10ms or higher	0.2V or below

Figure 54. Rise waveform diagram

OLVCC circuit

LVCC (VCC-Lockout) circuit prevents data rewrite operation at low power, and prevents wrong write. At LVCC voltage (Typ.=1.2V) or below, it prevent data rewrite.

8) Noise countermeasures

OVcc noise (bypass capacitor)

When noise or surge gets in the power source line, malfunction may occur, therefore, for removing these, it is recommended to attach a by pass capacitor $(0.1\mu F)$ between IC Vcc and GND, At that moment, attach it as close to IC as possible. And, it is also recommended to attach a bypass capacitor between board Vcc and GND.

OSK noise

When the rise time (tR) of SK is long, and a certain degree or more of noise exists, malfunction may occur owing to clock bit displacement. To avoid this, a Schmitt trigger circuit is built in SK input. The hysteresis width of this circuit is set about 0.2V, if noises exist at SK input, set the noise amplitude 0.2Vp-p or below. And it is recommended to set the rise time (tR) of SK 100ns or below. In the case when the rise time is 100ns or higher, take sufficient noise countermeasures. Make the clock rise, fall time as small as possible.

Notes for Use

- (1) Described numeric values and data are design representative values, and the values are not guaranteed.
- (2) We believe that application circuit examples are recommendable, however, in actual use, confirm characteristics further sufficiently. In the case of use by changing the fixed number of external parts, make your decision with sufficient margin in consideration of static characteristics and transition characteristics and fluctuations of external parts and our IC.
- (3) Absolute Maximum Ratings

If the absolute maximum ratings such as impressed voltage and operating temperature range and so forth are exceeded, IC may be destructed. Do not impress voltage and temperature exceeding the absolute maximum ratings. In the case of fear exceeding the absolute maximum ratings, take physical safety countermeasures such as fuses, and see to it that conditions exceeding the absolute maximum ratings should not be impressed to IC.

(4) GND electric potential

Set the voltage of GND terminal lowest at any operating condition. Make sure that each terminal voltage is not lower than that of GND terminal in consideration of transition status.

(5) Heat design

In consideration of allowable loss in actual use condition, carry out heat design with sufficient margin.

- (6) Terminal to terminal shortcircuit and wrong packaging When to package IC onto a board, pay sufficient attention to IC direction and displacement. Wrong packaging may destruct IC. And in the case of shortcircuit between IC terminals and terminals and power source, terminal and GND owing to foreign matter, IC may be destructed.
- (7) Use in a strong electromagnetic field may cause malfunction, therefore, evaluate design sufficiently

Ordering Information Product Code Description

	В	R	9	3	А	х	Х	Х	Х	-	W	М		х	Х
										-			-		
BUS Type 93 : Micro															
Operating	tempera	ature													
-40°C to +1	05°C														
Capacity							1								
46=1K	76=8	BK													
56=2K	86=	16K													
66=4K															
Package t	уре]						
F, RF	: SOF	2 8													
FJ, RFJ	: SOF	P-J8													
RFVT	: TSS	OP-B8													
RFVM	: MSC	DP8													
W : Double	e cell											1			
M : For Au	tomotive	Applicati	on												
Baakaga a															J

Package specifications

E2 : Embossed tape and reel (SOP8, SOP-J8, TSSOP-B8)

TR : Embossed tape nad reel (MSOP8)

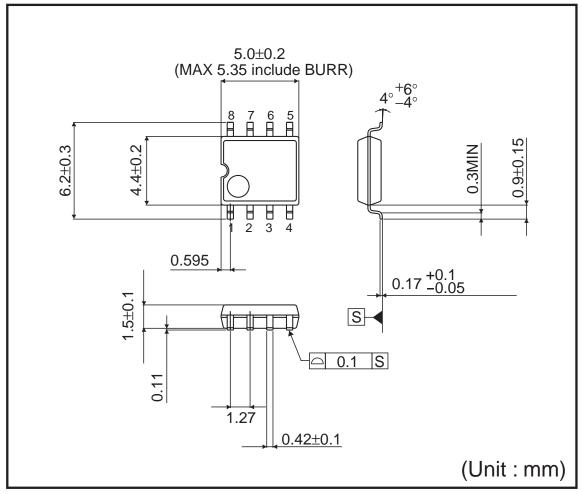
●Lineup

Consoity	Package		
Capacity	Туре	Quantity	
	SOP8	Reel of 2500	
1K	SOP-J8	Reel 01 2000	
IN	TSSOP-B8	Reel of 3000	
	MSOP8	Reel of 3000	
	SOP8	Deal of 2500	
2K	SOP-J8	Reel of 2500	
21	TSSOP-B8	Deal of 2000	
	MSOP8	Reel of 3000	
	SOP8	Deal of 2500	
4K	SOP-J8	Reel of 2500	
41	TSSOP-B8	Reel of 3000	
	MSOP8	Reel 01 3000	

Capacity	Package		
	Туре	Quantity	
8K	SOP8	Reel of 2500	
	SOP-J8	Reel 01 2500	
	TSSOP-B8	Reel of 3000	
	MSOP8	Reel 01 3000	
16K	SOP8	Reel of 2500	
	SOP-J8	Reel 01 2500	
	TSSOP-B8	Reel of 3000	
	MSOP8		

Physical Dimension Tape and Reel Information

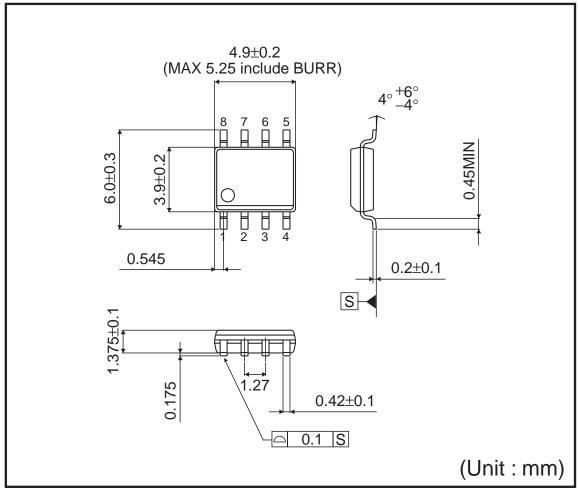
SOP8



<tape and="" information="" reel=""></tape>				
Таре	Embossed carrier tape			
Quantity	2500pcs			
Direction of feed	E2 (The direction is the 1pin of product is at the upper left when you hold reel on the left hand and you pull out the tape on the right hand			
Reel *Order quantity needs to be multiple of the minimum quantity.				

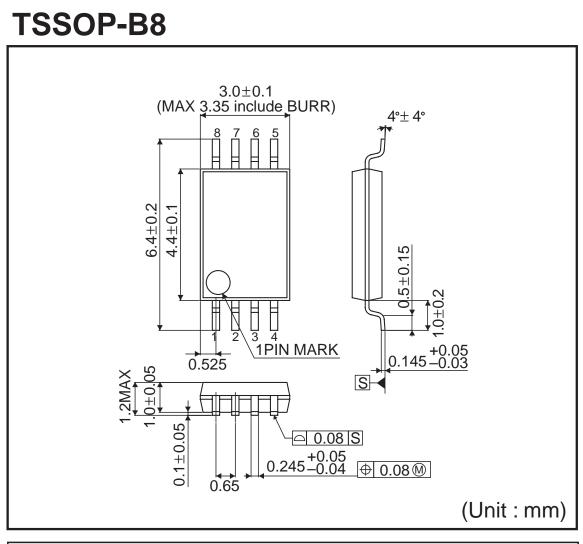
Physical Dimension Tape and Reel Information - Continued

SOP-J8



<tape and="" information="" reel=""></tape>			
Таре	Embossed carrier tape		
Quantity	2500pcs		
Direction of feed	E2 (The direction is the 1pin of product is at the upper left when you hold reel on the left hand and you pull out the tape on the right hand)		
	Precision of feed *Order quantity needs to be multiple of the minimum quantity		

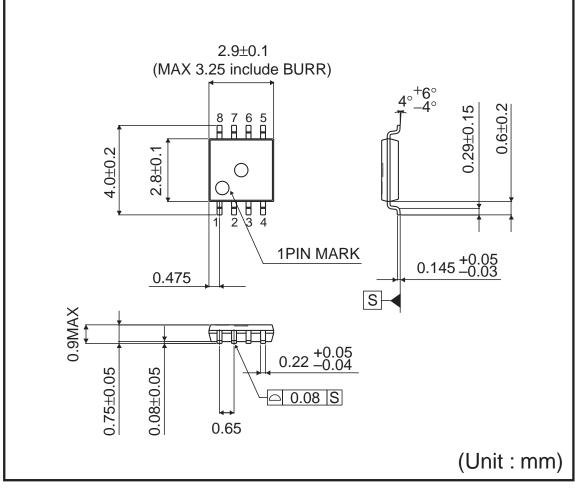
Physical Dimension Tape and Reel Information – Continued



<tape and="" information="" reel=""></tape>				
Таре	Embossed carrier tape			
Quantity	3000pcs			
Direction of feed	E2 (The direction is the 1pin of product is at the upper left when you hold reel on the left hand and you pull out the tape on the right hand			
	Pirection of feed *Order quantity needs to be multiple of the minimum quantity.			

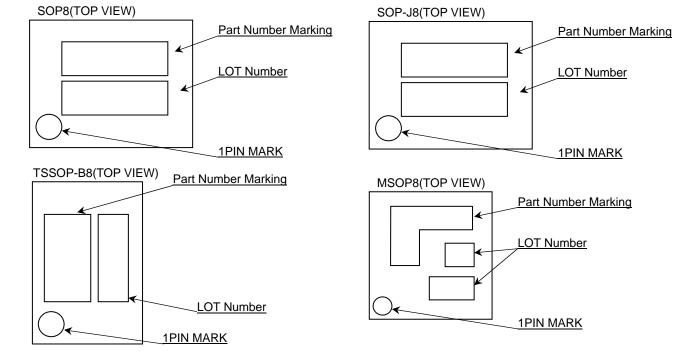
Physical Dimension Tape and Reel Information – Continued

MSOP8



<tape and="" information="" reel=""></tape>			
Таре	Embossed carrier tape		
Quantity	3000pcs		
Direction of feed	TR (The direction is the 1pin of product is at the upper right when you hold reel on the left hand and you pull out the tape on the right hand)		
	Reel *Order quantity needs to be multiple of the minimum quantity.		

Marking Diagrams



Marking Information

0	Product	Package Type	
Capacity	Name Marking		
	A46	SOP8	
	RA46		
	A46		
1K	RA46	SOP-J8	
	RA46	TSSOP-B8	
	RA46	MSOP8	
	A56		
	RA56	SOP8	
	A56		
2K	RA56	SOP-J8	
	RA56	TSSOP-B8	
	RA56	MSOP8	
	A66		
	RA66	SOP8	
417	A66		
4K	RA66	SOP-J8	
	RA66	TSSOP-B8	
	RA66	MSOP8	
	A76	0000	
	RA76	SOP8	
8K	A76	SOP-J8	
on	RA76	30P-Jo	
	RA76	TSSOP-B8	
	RA76	MSOP8	
	A86	SOP8	
	RA86	3060	
16k	A86	SOP-J8	
IOK	RA86		
	RA86	TSSOP-B8	
	RA86	MSOP8	

Revision History

Date	Revision	Changes
31.Aug.2012	001	New Release
4.Mar.2013	002	P.2 Add a Endurance limit at 60°C
6.Nov.2013	003	P.1 Added AEC-Q100 Qualified P.2 Changed Unit of Pd P.23 Update Product Code Description

Notice

Precaution on using ROHM Products

 If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

JAPAN	USA	EU	CHINA
CLASSII	CLASSⅢ	CLASS II b	CLASSI
CLASSⅣ	CLASSI	CLASSII	

2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:

[a] Installation of protection circuits or other protective devices to improve system safety

[b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure

- 3. Our Products are not designed under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
 - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

Precaution for Product Label

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

Precaution for Foreign Exchange and Foreign Trade act

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

Precaution Regarding Intellectual Property Rights

- 1. All information and data including but not limited to application example contained in this document is for reference only. ROHM does not warrant that foregoing information or data will not infringe any intellectual property rights or any other rights of any third party regarding such information or data.
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General Precaution

- 1. Before you use our Products, you are requested to carefully read this document and fully understand its contents. ROHM shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any ROHM's Products against warning, caution or note contained in this document.
- 2. All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using ROHM's Products, please confirm the latest information with a ROHM sales representative.
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